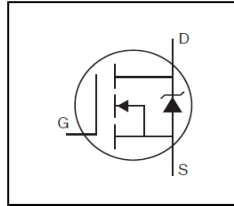


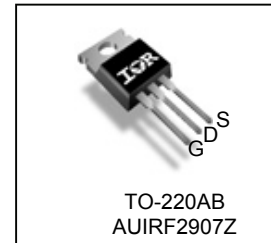
**Features**

- Advanced Planar Technology
- Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified \*



HEXFET® Power MOSFET

<b>V<sub>DSS</sub></b>	<b>75V</b>
<b>R<sub>DS(on)</sub> max.</b>	<b>4.5mΩ</b>
<b>I<sub>D</sub> (Silicon Limited)</b>	<b>170A</b>
<b>I<sub>D</sub> (Package Limited)</b>	<b>75A</b>



**Description**

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications

<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRF2907Z	TO-220	Tube	50	AUIRF2907Z

**Absolute Maximum Ratings**

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

Symbol	Parameter	Max.	Units
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V (Silicon Limited)	170	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V (Silicon Limited)	120	
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V (Package Limited)	75	
I <sub>DM</sub>	Pulsed Drain Current ①	600	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Maximum Power Dissipation	300	W
	Linear Derating Factor	2.0	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 20	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Thermally Limited) ②	270	mJ
E <sub>AS</sub> (Tested)	Single Pulse Avalanche Energy Tested Value ②	690	
I <sub>AR</sub>	Avalanche Current ①	See Fig.15,16, 12a, 12b	A
E <sub>AR</sub>	Repetitive Avalanche Energy ⑥		mJ
T <sub>J</sub>	Operating Junction and Storage Temperature Range	-55 to + 175	°C
T <sub>STG</sub>			
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case ⑧	—	0.50⑨	°C/W
R <sub>θCS</sub>	Case-to-Sink, Flat, Greased Surface ⑦	0.50	—	
R <sub>θJA</sub>	Junction-to-Ambient ⑦	—	62	

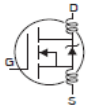
HEXFET® is a registered trademark of Infineon.

\*Qualification standards can be found at [www.infineon.com](http://www.infineon.com)

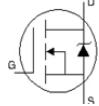
**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	75	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.069	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	3.5	4.5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 75A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Trans conductance	180	—	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 75A
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	20	μA	V <sub>DS</sub> = 75V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 75V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	200	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-200		V <sub>GS</sub> = -20V

**Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

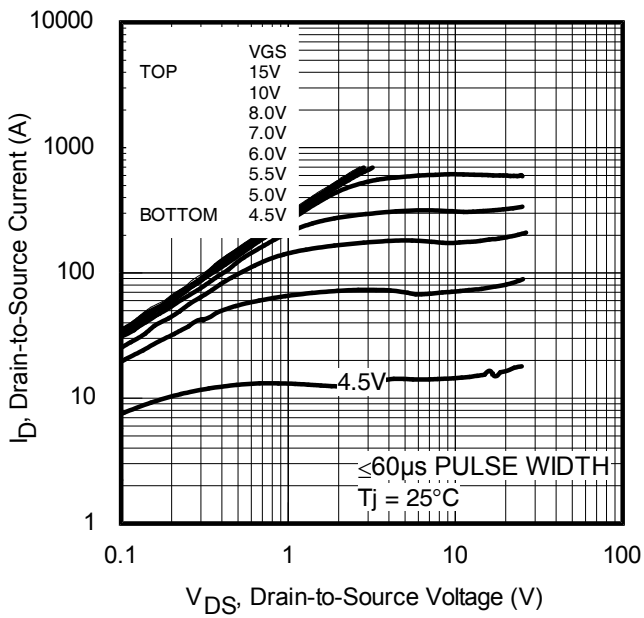
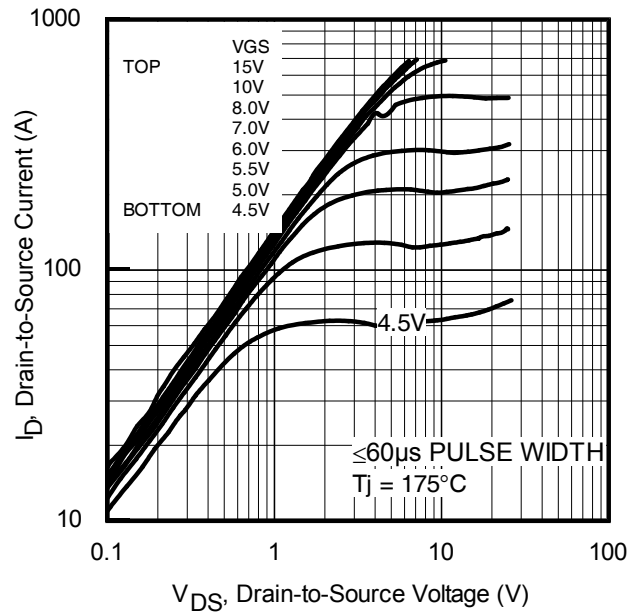
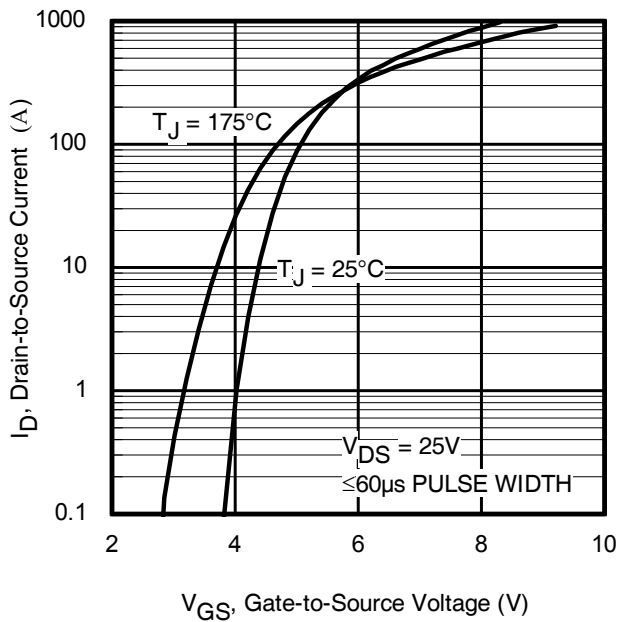
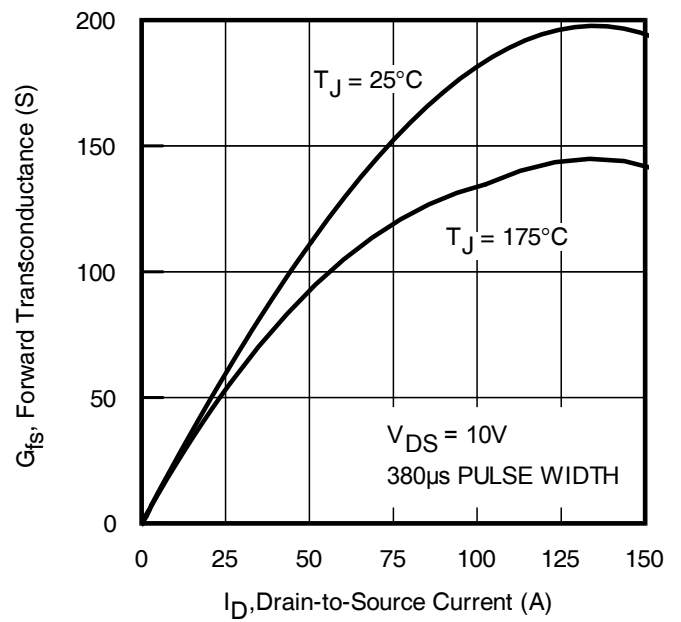
Q <sub>g</sub>	Total Gate Charge	—	180	270	nC	I <sub>D</sub> = 75A
Q <sub>gs</sub>	Gate-to-Source Charge	—	46	—		V <sub>DS</sub> = 60V
Q <sub>gd</sub>	Gate-to-Drain Charge	—	65	—		V <sub>GS</sub> = 10V ④
t <sub>d(on)</sub>	Turn-On Delay Time	—	19	—	ns	V <sub>DD</sub> = 38V
t <sub>r</sub>	Rise Time	—	140	—		I <sub>D</sub> = 75A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	97	—		R <sub>G</sub> = 2.5Ω
t <sub>f</sub>	Fall Time	—	100	—		V <sub>GS</sub> = 10V ④
L <sub>D</sub>	Internal Drain Inductance	—	5.0	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L <sub>S</sub>	Internal Source Inductance	—	13	—		
C <sub>iss</sub>	Input Capacitance	—	7500	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	970	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	510	—		f = 1.0MHz, See Fig. 5
C <sub>oss</sub>	Output Capacitance	—	3640	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 1.0V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	650	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 60V f = 1.0MHz
C <sub>oss eff.</sub>	Effective Output Capacitance	—	1020	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 60V

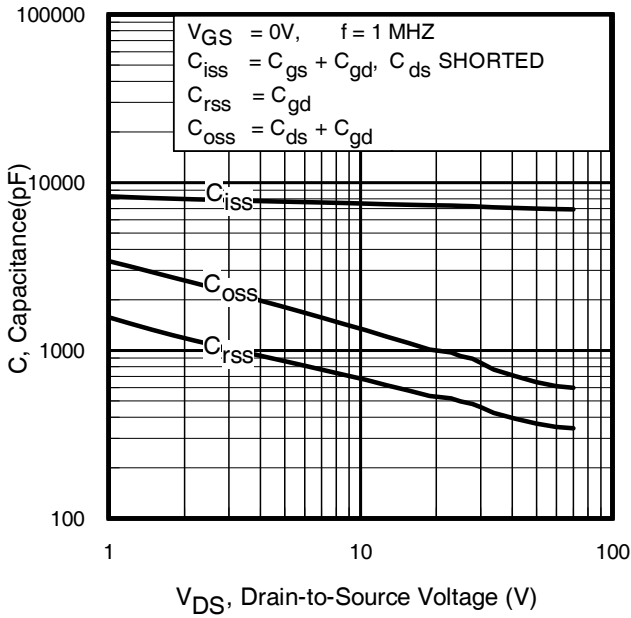
**Diode Characteristics**

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	75	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	680		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 75A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	41	61	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 75A, V <sub>DD</sub> = 38V
Q <sub>rr</sub>	Reverse Recovery Charge	—	59	89	nC	di/dt = 100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

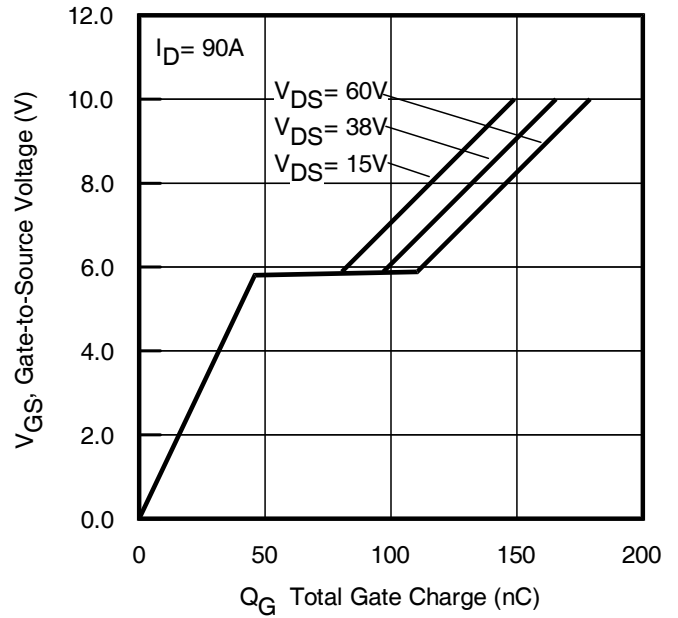
**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Limited by T<sub>Jmax</sub>, starting T<sub>J</sub> = 25°C, L = 0.095mH, R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 75A, V<sub>GS</sub> = 10V. Part not recommended for use above this value.
- ③ I<sub>SD</sub> ≤ 75A, di/dt ≤ 340A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ 175°C.
- ④ Pulse width ≤ 1.0ms; duty cycle ≤ 2%.
- ⑤ C<sub>oss eff.</sub> is a fixed capacitance that gives the same charging time as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 to 80% V<sub>DSS</sub>.
- ⑥ Limited by T<sub>Jmax</sub>, see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
- ⑦ This value determined from sample failure population, starting T<sub>J</sub> = 25°C, L = 0.095mH, R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 75A, V<sub>GS</sub> = 10V.
- ⑧ R<sub>θ</sub> is measured at T<sub>J</sub> of approximately 90°C.
- ⑨ TO-220 device will have an R<sub>th</sub> of 0.45°C/W.

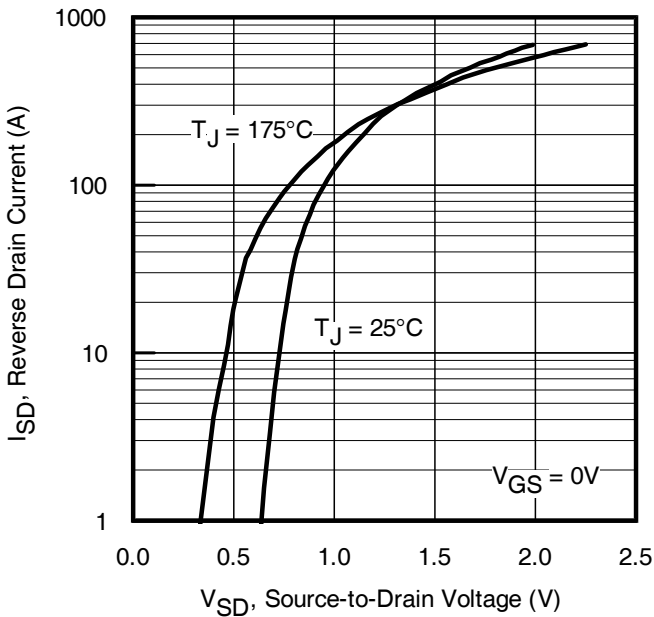

**Fig. 1** Typical Output Characteristics

**Fig. 2** Typical Output Characteristics

**Fig. 3** Typical Transfer Characteristics

**Fig. 4** Typical Forward Transconductance Vs. Drain Current



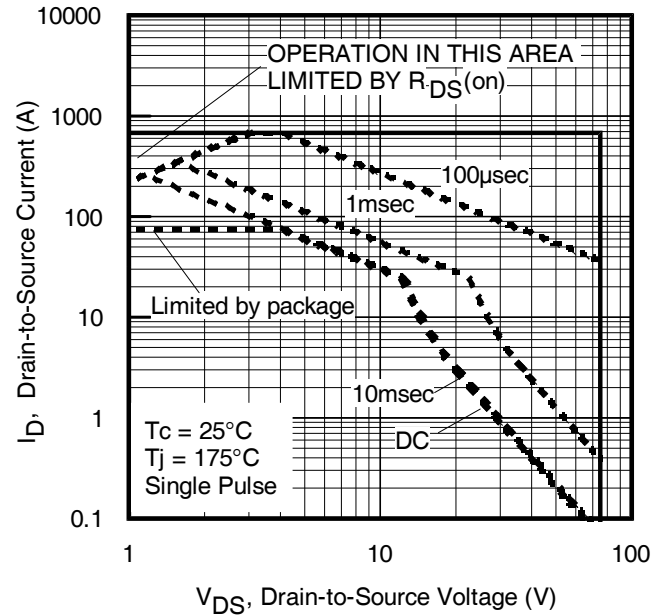
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



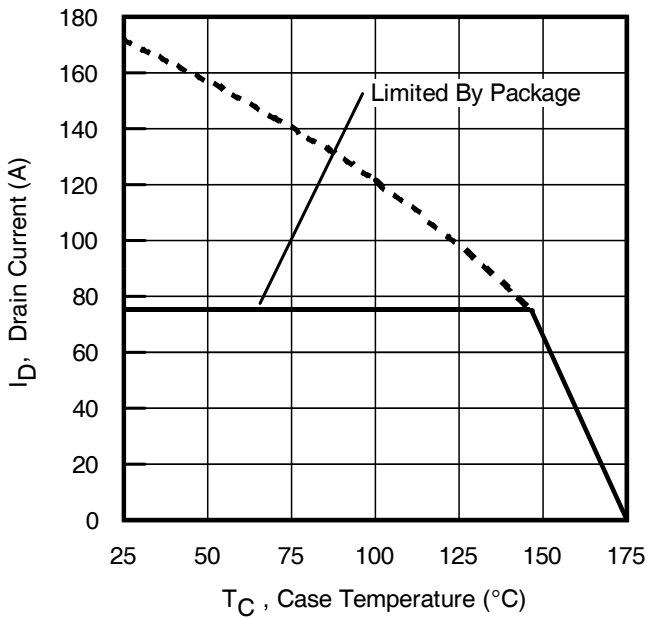
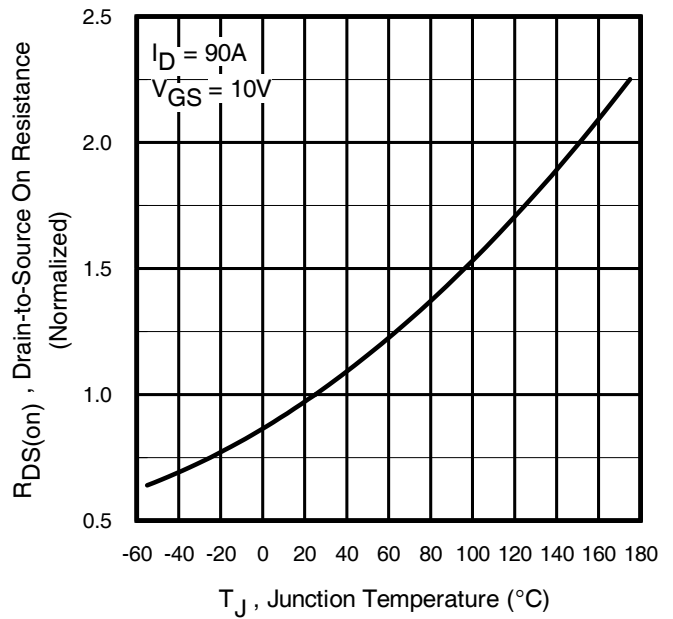
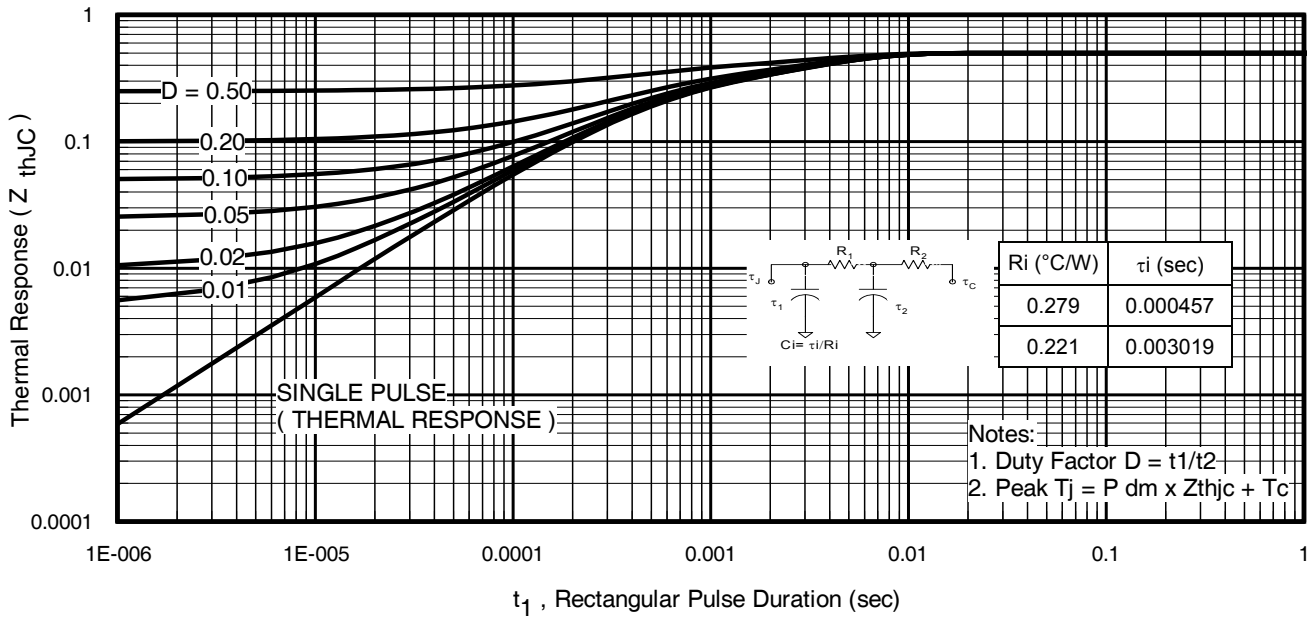
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage

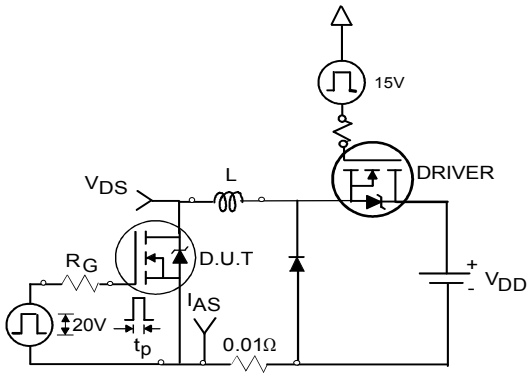
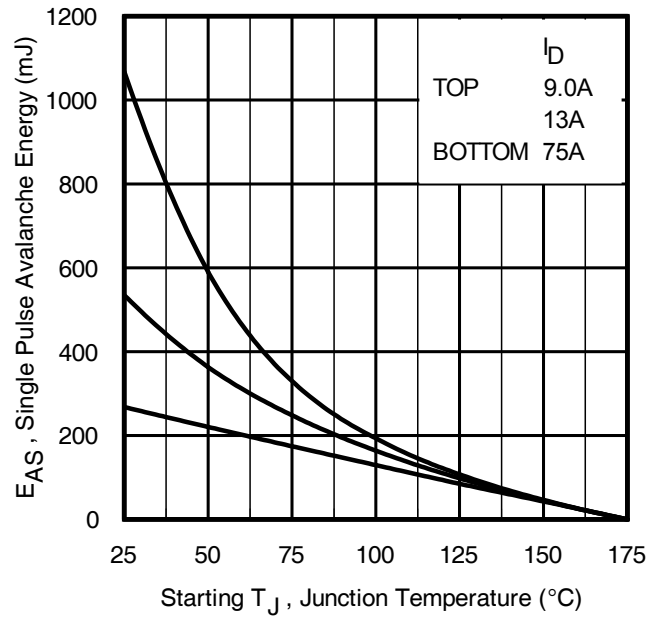
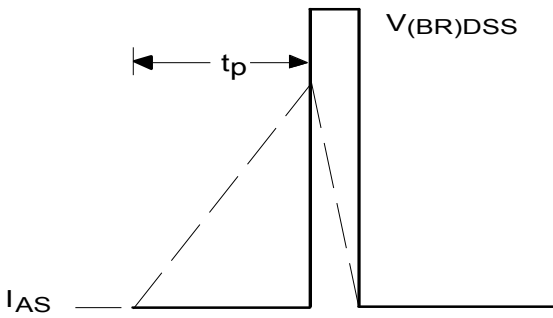
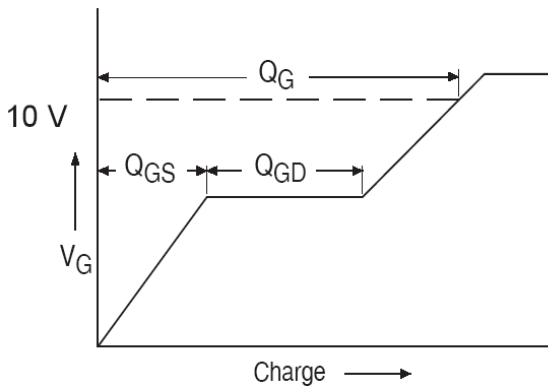
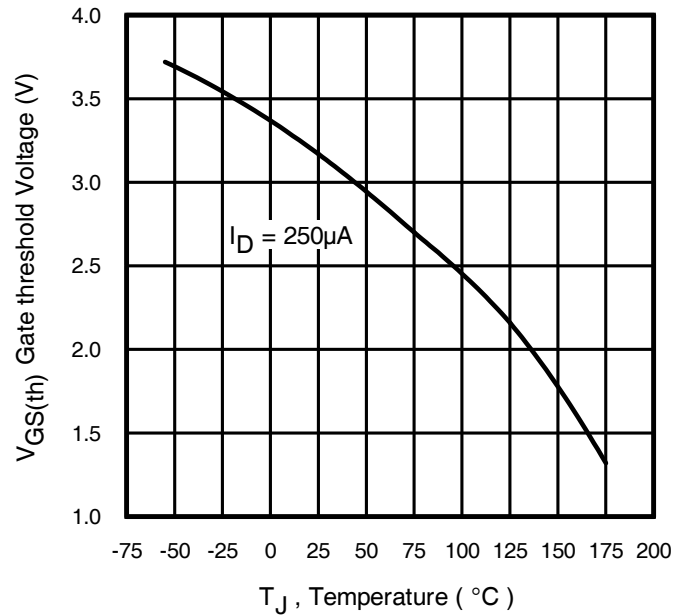
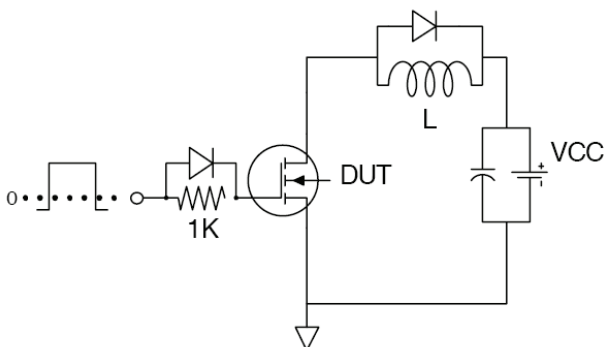


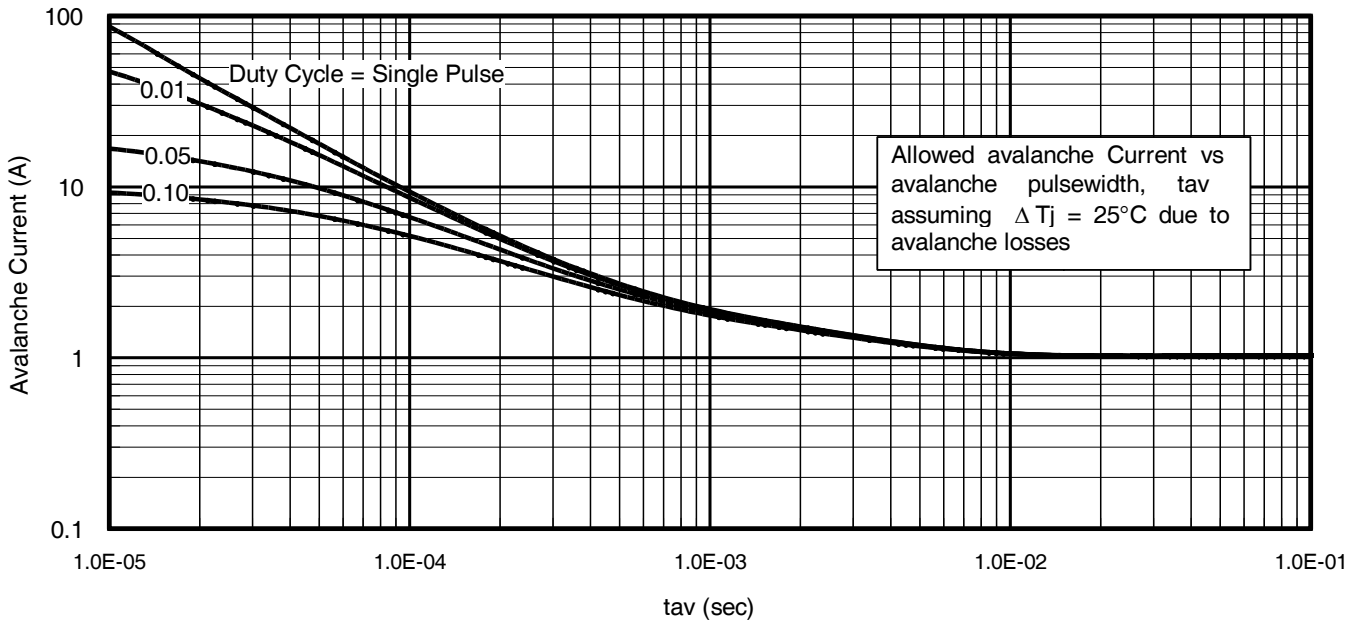
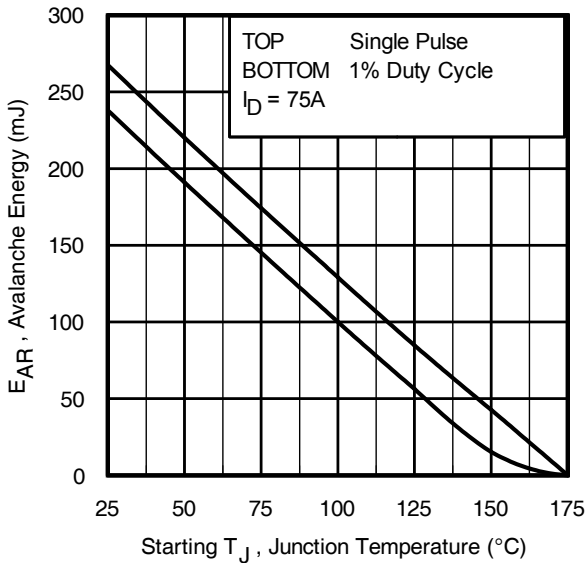
**Fig 7.** Typical Source-to-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area


**Fig 9.** Maximum Drain Current vs. Case Temperature

**Fig 10.** Normalized On-Resistance Vs. Temperature

**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case


**Fig 12a. Unclamped Inductive Test Circuit**

**Fig 12c. Maximum Avalanche Energy vs. Drain Current**

**Fig 12b. Unclamped Inductive Waveforms**

**Fig 13a. Gate Charge Waveform**

**Fig 14. Threshold Voltage vs. Temperature**

**Fig 13b. Gate Charge Test Circuit**


**Fig 15.** Typical Avalanche Current vs. Pulse width

**Fig 16.** Maximum Avalanche Energy vs. Temperature

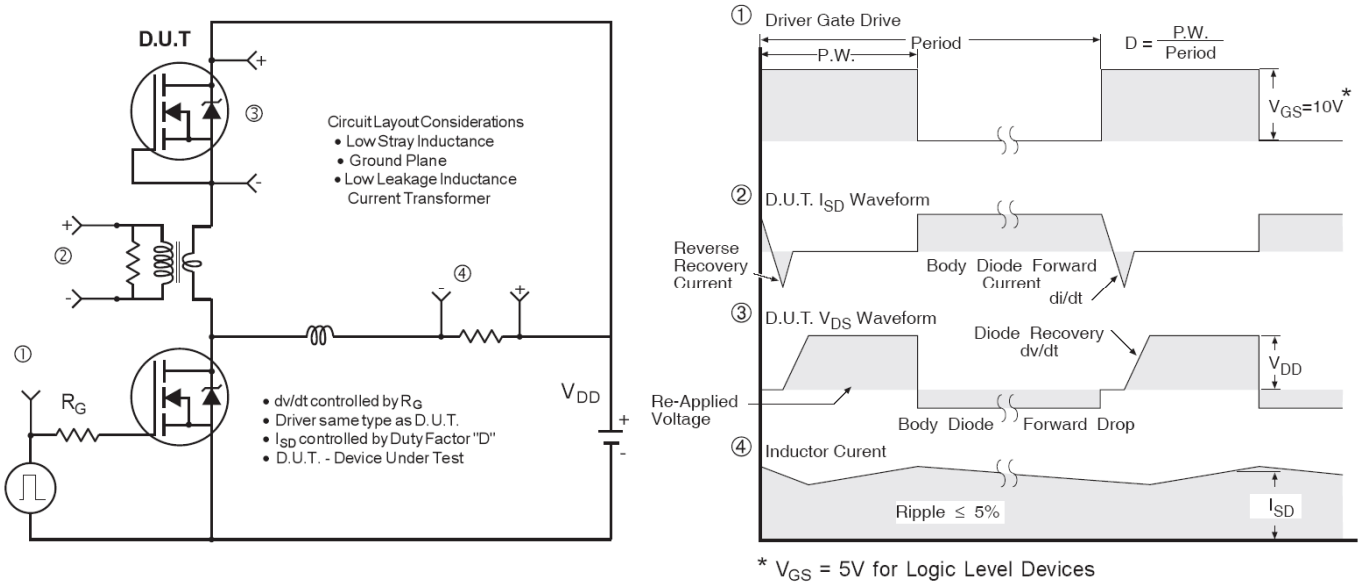
**Notes on Repetitive Avalanche Curves , Figures 15, 16:**  
**(For further info, see AN-1005 at www.infineon.com)**

1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5.  $BV$  = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 15, 16).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see Figures 11)

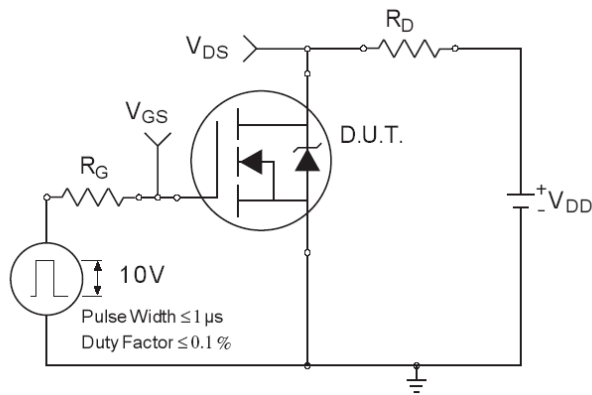
$$P_{D(ave)} = 1/2 ( 1.3 \cdot BV \cdot I_{av} ) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

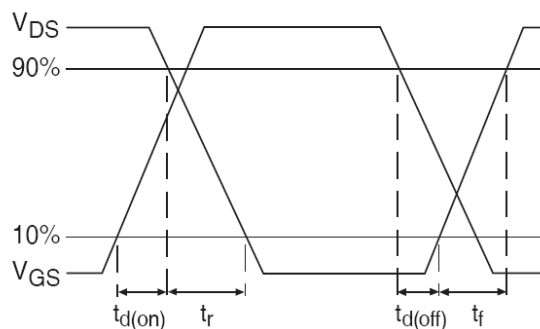
$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$



**Fig 17. Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs**

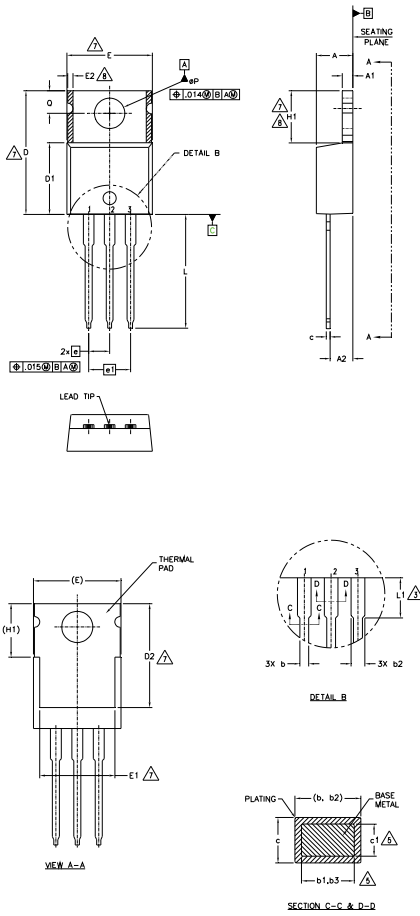


**Fig 18a. Switching Time Test Circuit**



**Fig 18b. Switching Time Waveforms**



**TO-220AB Package Outline (Dimensions are shown in millimeters (inches))**

**NOTES:**

- 1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4.- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 6.- CONTROLLING DIMENSION : INCHES.
- 7.- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8.- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
- 9.- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	1.14	1.40	.045	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		.100 BSC		
e1	5.08 BSC		.200 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
øP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

**LEAD ASSIGNMENTS**
**HEXFET**

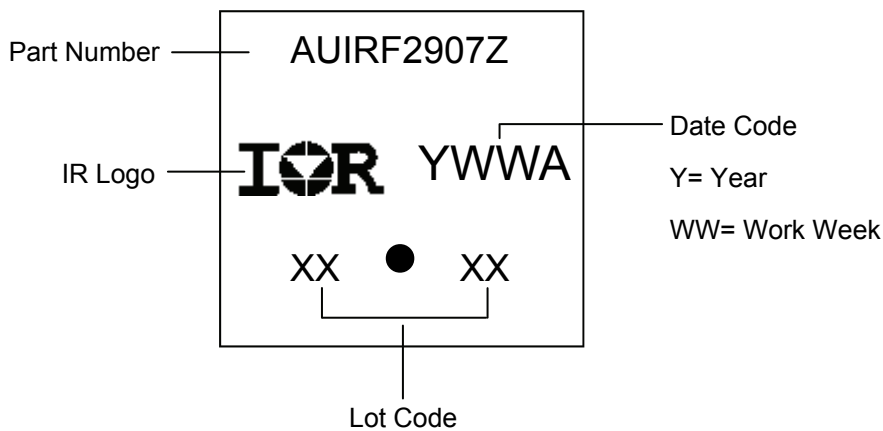
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

**DIODES**

- 1.- ANODE
- 2.- CATHODE
- 3.- ANODE

**TO-220AB Part Marking Information**


TO-220AB package is not recommended for Surface Mount Application.

**Qualification Information**

<b>Qualification Level</b>		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
<b>Moisture Sensitivity Level</b>		TO-220AB	N/A
<b>ESD</b>	Machine Model	Class M4 (+/- 425V) <sup>†</sup> AEC-Q101-002	
	Human Body Model	Class H2 (+/- 4000V) <sup>†</sup> AEC-Q101-001	
	Charged Device Model	Class C4 (+/- 1000V) <sup>†</sup> AEC-Q101-005	
<b>RoHS Compliant</b>		Yes	

† Highest passing voltage.

**Revision History**

Date	Comments
9/21/2017	<ul style="list-style-type: none"> <li>Updated datasheet with corporate template.</li> <li>Corrected typo error on package outline and part marking on page 9.</li> </ul>

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